NSN 5961-00-901-7403

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-901-7403 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.450 inches Overall Diameter: 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 3.5 gate trigger voltage, dc and 0.7 on-state voltage, dc **Current Rating Per Characteristic:** 16.00 amperes forward current, total rms nanoamperes and 40.00 milliamperes forward current, total rms preset **Maximum Operating Tempurature Per Measurement Point:** 85.0 degrees celsius case **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 1 case and 2 uninsulated wire lead w/terminal lug **Specification Data:** 80131-release3983 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: